

Title (en)
LOW VISCOSITY PRECURSOR COMPOSITIONS AND METHODS FOR THE DEPOSITION OF CONDUCTIVE ELECTRONIC FEATURES

Title (de)
NIEDERVISKÖSE PRECURSORZUSAMMENSETZUNGEN UND VERFAHREN ZUM AUFTRAGEN VON ELEKTRONISCH LEITFÄHIGEN STRUKTURELEMENTEN

Title (fr)
COMPOSITIONS DE PRECURSEUR A FAIBLE VISCOSITE ET PROCEDES DE DEPOT D'ELEMENTS ELECTRONIQUES CONDUCTEURS

Publication
EP 1448725 A2 20040825 (EN)

Application
EP 02773719 A 20021004

Priority
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Abstract (en)
[origin: WO03032084A2] Abstract A precursor composition for the deposition and formation of an electrical feature such as a conductive feature. The precursor composition advantageously has a low viscosity enabling deposition using direct-write tools. The precursor composition also has a low conversion temperature, enabling the deposition and conversion to an electrical feature on low temperature substrates. A particularly preferred precursor composition includes silver metal for the formation of highly conductive silver features. Another particularly preferred precursor composition includes copper metal for the formation of highly conductive copper features.

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C09D 11/00; H05K 1/09; H01B 1/02; B05D 5/06

IPC 8 full level
B41M 5/00 (2006.01); **B05D 3/02** (2006.01); **B05D 5/12** (2006.01); **B22F 9/30** (2006.01); **B41M 5/50** (2006.01); **B41M 5/52** (2006.01); **C09D 11/00** (2006.01); **C23C 18/06** (2006.01); **C23C 18/08** (2006.01); **C23C 20/04** (2006.01); **H01B 1/02** (2006.01); **H01L 21/28** (2006.01); **H01L 21/288** (2006.01); **H01L 21/316** (2006.01); **H01L 21/3205** (2006.01); **H05K 1/16** (2006.01); **H05K 3/10** (2006.01); **H01L 21/314** (2006.01); **H05K 1/03** (2006.01); **H05K 1/09** (2006.01); **H05K 3/12** (2006.01); **H05K 3/40** (2006.01)

CPC (source: EP KR US)
B05D 5/12 (2013.01 - KR); **B22F 9/30** (2013.01 - EP); **C09D 11/30** (2013.01 - EP); **C23C 18/06** (2013.01 - EP); **C23C 18/08** (2013.01 - EP US); **H01B 1/02** (2013.01 - KR); **H01B 1/026** (2013.01 - EP); **H05K 1/162** (2013.01 - EP); **H05K 3/105** (2013.01 - EP); **H01L 21/288** (2013.01 - EP); **H05K 1/0346** (2013.01 - EP); **H05K 1/097** (2013.01 - EP); **H05K 3/107** (2013.01 - EP); **H05K 3/125** (2013.01 - EP); **H05K 3/1258** (2013.01 - EP); **H05K 3/4061** (2013.01 - EP); **H05K 3/4069** (2013.01 - EP); **H05K 2201/09036** (2013.01 - EP); **H05K 2203/013** (2013.01 - EP); **H05K 2203/1142** (2013.01 - EP); **H05K 2203/121** (2013.01 - EP)

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